

## Role of Spin-Orbit Scattering in Nanostructured S/F Point Contacts

G. Goll<sup>1</sup>, M. Stokmaier<sup>1</sup>, C. Sürgers<sup>1,2</sup>, H. v. Löhneysen<sup>1,2,3</sup>

<sup>1</sup> Physikalisches Institut, Universität Karlsruhe, Wolfgang-Gaede-Str. 1, 76131 Karlsruhe

<sup>2</sup> Center for Functional Nanostructures, Universität Karlsruhe, 76128 Karlsruhe

<sup>3</sup> Forschungszentrum Karlsruhe, Institut für Festkörperphysik, 76021 Karlsruhe

We report on spin-dependent transport through nanosized Al/Fe point contacts. The contacts are prepared by electron-beam lithography in a silicon-nitride membrane and subsequent evaporation of the metal films on either side of the membrane [1,2]. The main advantage of this technique is the high stability of the nanostructured contacts which allows detailed investigations of the temperature and magnetic-field dependence of the current-voltage characteristics. By variation of the process parameters contacts with contact resistance  $R$  between  $R < 1 \Omega$  and almost  $30 \Omega$  are obtained. Andreev reflection of charge carriers at the interface between superconducting Al and ferromagnetic Fe is used as a tool to determine the spin polarization  $P$  of the transport current. The  $dI/dV$  vs.  $V$  spectra are measured in a dilution refrigerator at  $T < 1$  K and analysed in the framework of a model describing the transport through an S/F point contact with two spin-dependent transmission coefficients  $\tau_{\uparrow,\downarrow}$  [3]. Only spectra measured at  $T < 200$  mK  $\ll T_c^{Al}$  are considered for the analysis. The current spin polarization defined by  $P = |\tau_{\uparrow} - \tau_{\downarrow}|/(\tau_{\uparrow} + \tau_{\downarrow})$  is explored by varying the contact resistance  $R$  by about one order of magnitude.  $P$  is enhanced for high-ohmic contacts when the contact approaches the ballistic transport regime and scattering in the contact region is reduced. Assuming spin-orbit scattering as the main source of the reduction of  $P$ , with  $P(a) \sim \exp(-a/l_{so})$  where the contact radius  $a$  is deduced from the contact resistance  $R$  via the Wexler formula [4], a spin-orbit scattering length  $l_{so} \approx 280$  nm is obtained.

[1] K. S. Ralls *et al.*, Appl. Phys. Lett. **55**, 2459 (1989).

[2] F. Perez-Willard *et al.*, Phys. Rev. B **69**, 140502R (2004).

[3] A. Martin-Rodero *et al.*, Physica C **353**, 67 (2001).

[4] A. Wexler, Proc. Phys. Soc. **89**, 927 (1966).